

Conductivity, shot noise, and hot phonons in bilayer graphene

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We have studied electrical conductivity σ and shot noise of bilayer graphene sheets at high bias voltage V_{ds} . As a function of bias, we find linear increase of σ which is leveled off above $V_{ds} \sim 0.2$ V. We assign the saturation of σ to the creation of optical/zone boundary phonons. Excess noise Fano factor F is found to increase first with bias and reach a maximum at $V_{ds} \simeq 0.1$ V, above which F decreases as $V_{ds}^{-\gamma}$ with $\gamma = 0.25$ at the charge neutrality point. Using mean-free-path type of analysis we find a good agreement between the calculated and measured optical phonon temperatures.

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Monolayer and bilayer graphene are highly promising candidates for new semiconductor materials [1]. In monolayer form, it is gapless as its cone-like conduction and valence bands touch at two inequivalent Dirac points, where the density of states vanishes. The conductivity at the Dirac point, however, remains finite [1, 2] and the shot noise emulates that of a diffusive wire [3, 4, 5, 6]. Bilayer graphene has attracted large interest partly due to the fact that an energy gap could be opened by chemical doping [7] or by applying external electric field [8]. In general, the basic transport properties of bilayer graphene at the charge neutrality (or “Dirac”) point (CNP) are very close to monolayer graphene: their shot noise is expected to be equivalent [9] while the conductivity scales with the number of layers. When tuned away from the CNP, more involved behavior is predicted for the bilayer [9], though experimental verification of the differences is still missing, presumably due to disorder [10].

At large voltage bias, ballistic transport in both monolayer and bilayer graphene is expected to break down due to emission of optical phonons (OP), as has been observed in single-walled carbon nanotubes (SWNT) [11]. In monolayer graphene, the high bias behavior has been investigated by Meric *et al.* [12] who observed a tendency to current saturation due to OP emission. Electron-phonon (e-ph) scattering is detrimental for the speed and for the transconductance of graphene devices, whereas for the shot noise OP emission may contribute in a beneficial way by suppressing current fluctuations. Here we concentrate on bilayer graphene and report the first studies of shot noise in it. We show that at large bias voltages the shot noise is, indeed, decreased due to phonon emission.

Our theoretical treatment of resistance in a graphene bilayer is based on simple mean-free-path arguments, as has been done for example in Ref. 13 for SWNTs. The resistance R , dependent on drain-source voltage bias V_{ds} , is defined through the current $I(V_{ds}) = \frac{V_{ds}}{R(V_{ds})}$. We assume R to have the form [14] $R(V_{ds}) = R_{ball}(V_{ds}) \frac{L + l_{eff}(V_{ds})}{l_{eff}(V_{ds})} + R_c$. Here L is the length of the

sample, $R_{ball}(V_{ds}) = R_q/M_{eff}(V_{ds})$ is the conductance for a ballistic junction, with $R_q = h/2e^2$ the quantum resistance and $M_{eff}(V_{ds})$ an effective number of transverse modes within the transport window, and R_c is an additional “contact resistance”. Scattering is taken into account with an effective momentum-relaxation mean free path $l_{eff}(V_{ds})$. Using Matthiessen’s rule $l_{eff}(V_{ds}) = \left(l_{imp}^{-1} + l_{op,em}^{-1}(V_{ds}) + l_{op,abs}^{-1}(V_{ds}) \right)^{-1}$, where the individual mean free paths are due to impurities, OP emission, and OP absorption, respectively; acoustic phonon scattering is neglected due to its weakness [15, 16]. Here l_{imp} also depends on the carrier density n (or gate voltage V_g) as well as the impurity density n_{imp} [17]. $M_{eff}(V_{ds})$ too depends on V_g via the Fermi energy.

We assume that all the relevant OPs have the same energy $\hbar\Omega \approx 0.2$ eV, and that they all have the same occupation number $N_{op} = N(T_{op})$. Here T_{op} is the corresponding temperature, and we define $N(T) = 1/(\exp(\hbar\Omega/k_B T) - 1)$. The bath temperature $T = T_0$ determines the equilibrium occupation $N_0 = N(T_0)$. For emission, we assume $l_{op,em}(V_{ds}) = L \frac{\hbar\Omega}{|eV_{ds}|} + l_{e-op} \frac{N_0 + 1}{N_{op} + 1}$, where the first term is the distance needed for the electrons to reach the threshold energy $\hbar\Omega$ for OP emission and the second term is the mean free path after the threshold has been exceeded [11, 13]. For absorption, we take $l_{op,abs}(V_{ds}) = l_{e-op} \frac{N_0 + 1}{N_{op}}$. It is expected that when $|V_{ds}| \rightarrow \infty$, then $N_{op} \rightarrow \infty$, and so $l_{op,em}, l_{op,abs} \rightarrow 0$.

To find out the stationary-state V_{ds} -dependence of N_{op} or, equivalently, of T_{op} , a heat balance equation must be solved self-consistently with the current. We employ similar heat flow schematics as for SWNTs [13, 18]. The bottleneck in the heat transfer from the electrons to the substrate is assumed to be due to the decay of OPs into acoustic or substrate phonons (see also Ref. 19), and the latter are assumed to remain at $T = T_0$. The power that heats the OP system is $P = P_{Joule} - P_{diff}$. Here $P_{Joule} = I^2(R - R_c)$ is the Joule power and $P_{diff} = 2\pi^2(k_B/e)^2(T_e^2 - T_0^2)/(R - R_c)$ is the power transferred from the electrons to the leads. Here T_e is

an average electron temperature. In stationary state $P = P_{e-op} = P_{op-ac}$, where we approximate $P_{e-op} = N_c \hbar \Omega (N(T_e) - N_{op}) / \tau_{e-op}$ and $P_{op-ac} = N_c \hbar \Omega (N_{op} - N_0) / \tau_{op-ac}$. Here P_{e-op} and τ_{e-op} (P_{op-ac} and τ_{op-ac}) are an electron-OP (OP-acoustic phonon) power transfer and relaxation time, respectively. Assuming that $\tau_{e-op} \ll \tau_{op-ac}$ [20], we find $T_e \approx T_{op}$, where T_{op} is given by $N_{op} = N_0 + P / (N_c \hbar \Omega / \tau_{op-ac})$. The parameter N_c is an effective number of occupied modes on the various OP branches. A value $N_c \ll LW/A_c$, where W is the width of the sample and A_c the unit cell area, models the nonuniformity of the OP distribution over the phase space [21]. We note that some of the above approximations may only be justified for $V_{ds} \gtrsim 0.2$ V, where both e-op and electron-electron (e-e) scattering are strong.

The lower two electronic energy bands of a bilayer are given by $E(k) = \pm(\sqrt{t_\perp^2 + (2\hbar v_F k)^2} - t_\perp)/2$, where $t_\perp = 0.4$ eV is the interlayer coupling and $v_F = 1.1 \cdot 10^6$ m/s [1]. This yields the number of ballistic propagating transverse modes at energy E : $M(E) = \frac{2W}{\pi \hbar v_F} \sqrt{E^2 + t_\perp^2} |E|$. At $V_{ds} \gtrsim t_\perp/e$ also the higher bilayer bands should begin to contribute, but we neglect them, assuming the scattering from phonons to be very strong there. Using this we estimate $M_{eff}(V_{ds}) = \frac{1}{|eV_{ds}|} \int_\mu^{\mu+|eV_{ds}|} M(E) dE$. The effective Fermi energy $\mu > 0$ is used to model the presence of charge puddles and evanescent modes, such that a residual carrier density n^* remains also at the CNP [22]. We use the form $\mu = \sqrt{(n^*)^2 + (C_g |V_g - V_{g,CNP}|/e)^2} / \frac{dn}{d\mu}$, where C_g is the specific gate capacitance and $\frac{dn}{d\mu} = \frac{t_\perp}{\pi \hbar^2 v_F^2}$ is the density of states.

Shot noise has turned out to be very useful in the studies of graphene [5, 6]. At the zero frequency limit, shot noise is given by the correlation function of current fluctuations $\delta I(t)$: $S_I = \int dt \langle \delta I(t) \delta I(0) \rangle$ [23]. Typically, the strength of shot noise is given by the Fano factor, defined as $\mathfrak{F} = S_I / 2e \langle I \rangle$. For bilayer graphene, theoretical calculations give either $\frac{1}{3}$ [9] or $1 - \frac{2}{\pi}$ [3], i.e. very close to what has been observed at the CNP in monolayers [5, 6].

At high bias, inelastic OP scattering reduces S_I in general. The role of inelastic scattering on the shot noise in diffusive conductors has been investigated by Nagaev [25] and by Naveh et al. [26]. They find a power law decrease of the Fano factor $\mathfrak{F} \sim \beta^{-2/5}$ where $\beta = L/l_{in} > 10$, $l_{in} = (l_{op,em}^{-1}(V_{ds}) + l_{op,abs}^{-1}(V_{ds}))^{-1}$. The result is based on a solution of the Boltzmann equation and the exponent of the power law reflects the e-ph collision kernel which is sensitive to the dimensionality of the sample, to the nature of the phonons, as well as to the details of the thermal transport. For 1D phonons, the Boltzmann equation yields $\mathfrak{F} \propto V_{ds}^{-1/3}$.

The above result can be obtained using a heating model [27] which assumes that one can define a local temperature $T(x)$ along the sample, independent of the transverse dimension of the sheet. Moreover, this model

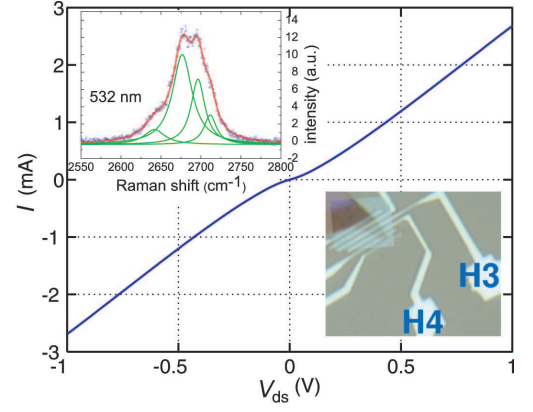


FIG. 1: (Color online) $I(V_{ds})$ curve measured between the terminals H3 and H4 on a $0.3 \times 1.3 \mu\text{m}^2$ sheet at 4.2 K at the CNP. Optical interferogram of the sample is illustrated in the right inset. To make the sheet more visible, digital contrast enhancement has been applied. The upper inset displays our typical bilayer Raman spectrum with four lines fitted.

yields a simple relation for the Fano factor

$$\mathfrak{F} = \frac{2k_B T_e}{eV_{ds}}, \quad (1)$$

where $T_e = \frac{1}{L} \int_0^L T(x) dx$ is the average electronic temperature. This result is valid when either e-ph or e-e collision rate is large and local equilibrium is approached. In graphene both e-op and e-e scattering are strong and bias dependent [16]: the e-e mean free path is $\sim L$ already at $V_{ds} \sim 0.1$ V.

Inelastic scattering by e-e interaction can also lead to an increase of the Fano factor. This takes place if the heat carried away via the electron-phonon coupling is small compared with the (electronic) heat diffusion along the graphene sheet to the metallic contacts. With uniform resistivity and Wiedemann-Franz law, the above integral yields $T_e = \frac{\sqrt{3}}{8} V_{ds}$, i.e. $\mathfrak{F} = \frac{\sqrt{3}}{4}$ [23] for hot electrons in local thermal equilibrium. Now, if heat leaks out from the system via e-ph coupling, the ratio $k_B T_e / eV_{ds}$ goes down and $\mathfrak{F}$ decreases. Hence, we expect to have two opposite tendencies for $\mathfrak{F}(V_{ds})$, but at very large bias, the e-ph coupling will dominate and reduce the noise.

We have measured three bilayer graphene samples having $L = 300$ nm and widths $W = 1.0, 1.3$, and $1.6 \mu\text{m}$, respectively. The samples were contacted using Ti/Al/Ti sandwich structures with thicknesses $10 \text{ nm} / h / 5 \text{ nm}$ where h was varied over $50 - 70$ nm (10 nm of Ti is the contact layer). A set of $0.3 - 0.6 \mu\text{m}$ wide contacts, $2 - 6$ per sheet, were patterned using e-beam lithography. The strongly doped Si substrate was used as a back-gate, separated by 250 nm of SiO_2 from the sample. All the data were measured at $T_0 = 4.2$ K using a two-lead configuration. Differential AC-conductivity was recorded at frequency $f = 32$ Hz while the excess noise

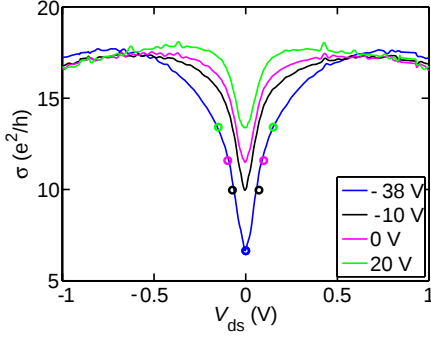


FIG. 2: (Color online) Differential conductivity σ for bilayer sample with $L = 0.3 \mu\text{m}$ and $W = 1.3 \mu\text{m}$. versus V_{ds} . The gate voltage values are indicated in the image. The CNP is located at $V_g = V_{g,CNP} = -38 \text{ V}$ (lowest curve). The circles show the dependence of $\sigma(V_{ds} = 0)$ on V_g scaled to the V_{ds} axis, as discussed in the text.

$F = (S_I(I) - S_I(0))/(2eI)$ was integrated over the range $f = 600 - 900 \text{ MHz}$. The relation between F and the true Fano factor $\mathfrak{F}$ is given by

$$F = \mathfrak{F} \cdot \left[\left(\frac{eV_{ds}}{2k_B T} \coth \frac{eV_{ds}}{2k_B T} - 1 \right) / \frac{eV_{ds}}{2k_B T} \right]. \quad (2)$$

For further techniques, we refer to Ref. 5.

The $I(V_{ds})$ curve of our $0.3 \times 1.3 \mu\text{m}^2$ sample is illustrated in Fig. 1. It displays non-linear behavior [28] at small drain-source voltage V_{ds} ; the nonlinearity depends on the gate voltage V_g and it is largest near the CNP. The non-linear behavior can be observed more clearly in Fig. 2 which displays the differential conductivity $\sigma = \frac{L}{W} \frac{dI}{dV_{ds}}$ of the same sample at a few values of V_g . We measured the minimum zero-bias conductivities $\sigma_0 = 6.5, 5.5$, and $4.7e^2/h$ for our samples of size 0.3×1.3 , 0.3×1.6 , and $0.3 \times 1.0 \mu\text{m}^2$, respectively. The enhancement from the universal value $2 \times 4e^2/\pi h \approx 2.5e^2/h$ [9] suggests the presence of impurities in these samples.

A nearly linear increase in σ is seen at $V_{ds} = 40 - 200 \text{ mV}$ in Fig. 2; the slope of the increase depends weakly on the distance from the CNP which is located at $V_g = V_{g,CNP} = -38 \text{ V}$. The increase in σ is an indication that M_{eff} grows as the bias window is increased. Below 40 mV , the conductance displays interference phenomena (not shown), reminiscent of the Fabry-Pérot oscillations observed by Miao et al [2]. The growth in σ slows down above 0.2 V and a saturation is reached above $V_{ds} = 0.5 \text{ V}$. At larger V_{ds} , even a down turn of σ is found. This indicates a tendency towards saturation of current, although it's clearly much weaker than typically seen for carbon nanotubes [11] or recently in monolayer graphene [12, 29]. However, our samples are much shorter than those of Refs. [12, 29], and the saturation is known to be weak for short nanotubes [30].

Figure 3a illustrates conductivity results of our model

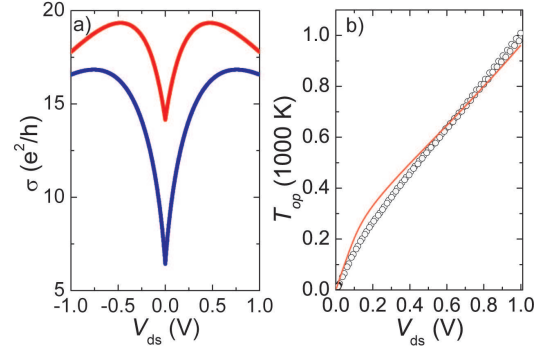


FIG. 3: (Color online) a) Result of our model for the CNP (lower curve, $V_g = -38 \text{ V}$ in Fig. 2) and for $V_g = V_{g,CNP} + 38 \text{ V}$ using parameters given in the text. b) Electron temperature T_e as deduced from measured shot noise using Eq. (1) (o), and OP temperature $T_{op} = \frac{\hbar\Omega}{k_B \ln((N_{op}+1)/N_{op})}$ from our model with the same parameters as in (a) (solid line).

calculation using the parameters: $\hbar\Omega = 0.18 \text{ eV}$, $C_g = 100 \text{ aF}/\mu\text{m}^2$ (see below), $R_c = 70 \Omega$ per contact, $n_{imp} = 9 \cdot 10^{10} \text{ cm}^{-2}$, $l_{e-op} = 15 \text{ nm}$, $\tau_{op-ac} = 5 \text{ ps}$, $N_c = 0.2(LW/A_c)$, and $n^* = 9 \cdot 10^{11} \text{ cm}^{-2}$. Here the V_g dependence of $\sigma(V_{ds} = 0)$ fixes n_{imp} and n^* , while SWNT values are used for τ_{op-ac} [21] and l_{e-op} [13] (see also Ref. [20]). Note that N_c and τ_{op-ac} only appear in the combination $N_c \hbar\Omega / \tau_{op-ac}$. It should also be noted that the independence of the contact resistance on V_g was recently shown by Russo *et al.* [31] to be a good approximation. Furthermore, the fit is done bearing in mind the OP temperature deduced from shot noise measurements (see below). The agreement between the model and the experimental results is good.

The finding, implicit in the above fitting, that $\sigma(V_{ds})$ is related to the effective number of modes in graphene can be given further support by comparing the measured V_{ds} - and V_g -dependencies of σ . We find linear scaling $\sigma(V_{ds} = 0, V_g = \frac{dn}{d\mu} \frac{e^2}{C_g} V) = \sigma(V_{ds} = V, V_g = 0)$. Fitting this to the data (see Fig. 2) yields the value $C_g = 100 \text{ aF}/\mu\text{m}^2$ used above, which is close to the theoretical parallel-plate value $C_g = 140 \text{ aF}/\mu\text{m}^2$.

The measured excess noise Fano factor F is illustrated in Fig. 4 for our $0.3 \times 1.3 \mu\text{m}^2$ sample on log-log scale. Owing to its definition, F increases first linearly in the cross-over regime between thermal and shot noise. The dashed curve, fitted to the low-bias data at the CNP ($V_g = -38 \text{ V}$) indicates the behavior obtained from Eq. (2) using $\mathfrak{F} = 0.28$. One can see that at intermediate bias, $V_{ds} = 50 - 100 \text{ mV}$, the Fano factor grows beyond the low-bias value, indicating overheating of electrons in the sample. However, the observed value is well below $\mathfrak{F} = \sqrt{3}/4$ so that we do not reach pure hot electron regime. Using small bias fits $V_{ds} < 40 \text{ mV}$, we find $\mathfrak{F} =$

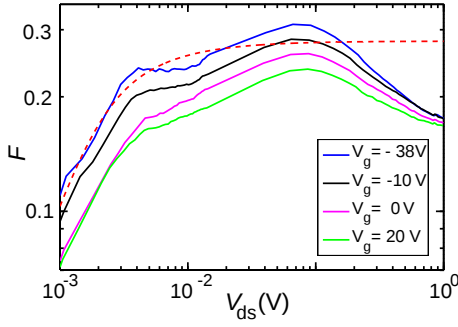


FIG. 4: (Color online) Excess noise Fano factor $F = (S_I(I) - S_I(0))/(2eI)$ vs. bias voltage V_{ds} at three values of V_g indicated in the figure (from top to bottom). The dashed curve is calculated using Eq. (2) for $\mathfrak{F} = 0.28$.

0.23 and $\mathfrak{F} = 0.2$ for our other two samples at the CNP. These values fall somewhat short from the values of $\mathfrak{F} = 1 - 2/\pi, 1/3$ calculated theoretically for bilayer graphene [9, 24]. However, disorder may decrease shot noise and improve the agreement (see e.g. Refs. 32, 33).

All the traces in Fig. 4 display a maximum near $V_{ds} = 0.08$ V, nearly independent of the gate voltage value although the actual maximum value for F decreases from 0.31 at the CNP down to 0.23 far away from it. We note that the position of the maximum coincides with the inflection point of $\sigma(V_{ds})$ (see Fig. 2). Above 0.1 V, all the curves display a power law decrease $F \propto V_{ds}^{-\gamma}$ with an exponent $\gamma = 0.25 - 0.13$. The decrease in F already at $V_{ds} \sim 0.1$ V suggests that there are active OP modes around 100 meV as well. We have also checked our $0.3 \times 1.3 \mu\text{m}^2$ sample with a 15 nm thick hafnium oxide ALD coating on it and obtained different exponents, which fits the expectations as the Coulomb screening and the OPs become both modified.

Taken together, all evidence indicates short inelastic mean free path at $V_{ds} \gtrsim 0.1$ V. Consequently, we argue that local $T(x)$ is well defined at large bias and that shot noise can be employed to determine the electronic temperature T_e according to Eq. (1). Fig. 3b displays T_e at the CNP obtained from the data in Fig. 4. For comparison, we have plotted the OP temperature T_{op} from our model. The agreement is good, and we conclude that both the electrons and the OPs heat up to 1000 K in our measurements.

We have presented data on high bias electric transport on bilayer graphene sheets with disorder. At $V_{ds} > 0.1$ V, we observe a decrease of Fano factor in a power-law fashion, which can be interpreted as shot noise reduction by optical/zone boundary phonons with energy $\hbar\Omega \sim 0.2$ eV. Using a model for resistance, based on simple mean-free-path type of arguments, we find an optical phonon mean free path which is close to that determined in SWNTs. At bias voltages of 0.5 - 1 V, we find a saturat-

tion and a slight decrease of conductivity due to phonon scattering; T_{op} given by our model agrees well with the values deduced from shot noise measurements.

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